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PCT

PATENT

IN THE UNITED STATES PATENT
AND TRADEMARK OFFICE

Applicants: Gogolides et al.

Serial No.: 10/516,384

Filed: May 30, 2003

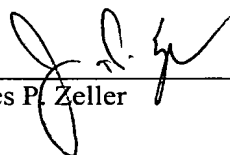
For: LITHOGRAPHIC
MATERIALS BASED ON
POLYMERS CONTAINING
POLYHEDRAL OLIGOMERIC
SILSESQUIOXANES

Group Art Unit: To be assigned

Examiner: To be assigned

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James P. Zeller

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
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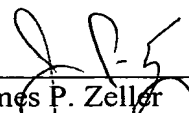
Sir:

The patents listed on the enclosed Form PTO-1449 are identified pursuant to 37 CFR
§§ 1.56, 1.97, and 1.98. Copies of the patents are included as required.

Entry and consideration of the submitted documents are solicited.

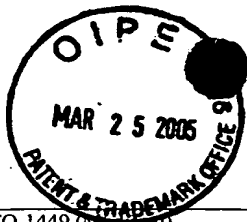
Respectfully submitted,

MARSHALL, GERSTEIN & BORUN LLP

By: 
James P. Zeller
Reg. No. 28,491
Attorneys for Applicants

March 21, 2005

6300 Sears Tower
233 South Wacker Drive
Chicago, Illinois 60606-6357
(312) 474-6300



Form PTO-1449 (Revised)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 30848/40704	Serial No. 10/516,384
INFORMATION DISCLOSURE STATEMENT		Applicant Gogolides et al.	
		Filing Date May 30, 2003	Group

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
	"Double Layer Resist System for High Resolution Lithography", Hatzakis et al., Proc. Microcircuit Engnrg. Lausanne, 1981, pp. 386-396
	"Linear Hybrid Polymer Building Blocks: Methacrylate-Functionalized Polyhedral Oligomeric Silsesquioxane Monomers and Polymers", Lichtenhan et al., Macromolecules 28, 1995, pp. 8435-8437
	"Extension of 248 nm Optical Lithography: A Thin Film Imaging Approach", Lin et al., SPIE Vol. 3333, 1998, pp. 278-288
	"Outlook for 157-nm Resist Design", Kunz et al., SPIE Vol. 3678, March 1999, pp. 13-20
	"Incorporation of Polyhedral Oligosilsesquioxane in Chemically Amplified Resists to Improve Their Reactive Ion Etching Resistance", Wu et al., J. Vac. Sci. Technol. B 19(3), May/June 2001, pp. 851-855
	"Novel CA Resists with Photoacid Generator in Polymer Chain", Wu et al., SPIE Vol. 4345, 2001, pp. 521-527
	"Novel Positive-Tone Chemically Amplified Resists with Photoacid Generator in the Polymer Chains", Wu et al., Adv. Mater 13, No. 9, May 2001, pp. 670-672
	"Silicon-Containing Resists for 157 nm Applications", Sooriyakumaran et al., SPIE Vol. 4345, 2001, pp. 319-326
	"Recent Advances in Resists for 157 nm Microlithography", Trinquet et al., J. Vac. Sci. Technol. B 20(2), March/April 2002, pp. 531-536
	International Search Report in PCT/GB03/00018 dated September 23, 2003

Examiner	Date Considered
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	